NSN 5961-01-281-5577



Diode Semiconductor Device - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5961-01-281-5577 **Inclosure Material:** Ceramic or glass **Overall Length:** 0.570 inches **Terminal Length:** Between 1.000 inches and 1.625 inches **Overall Diameter:** Between 0.215 inches and 0.235 inches **Function For Which Designed:** Transient suppressor Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-13 **Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method: Terminal Features Provided:** Quality assurance level txv **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 15.2 breakdown voltage, dc and 16.8 breakdown voltage, dc **Current Rating Per Characteristic:** 5.00 microamperes forward current, average peak **Power Rating Per Characteristic:** 1.0 watts small-signal input power, common-collector major **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Precious Material And Location:** Terminal surfaces silver **Precious Material:** Silver **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:**

N/a

Shelf Life:

Unit Of Measure:

81349-mil-s-19500/500 government specification

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